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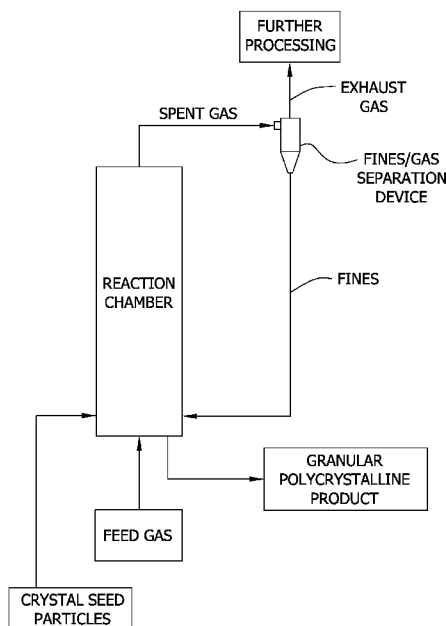
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(54) Title: METHODS FOR INCREASING POLYCRYSTALLINE SILICON REACTOR PRODUCTIVITY BY RECYCLE OF SILICON FINES

FIG. 2



(57) Abstract: Processes for producing polycrystalline silicon include contacting silicon particles with a thermally decomposable silicon compound in a reaction chamber. A portion of the silicon decomposable compound decomposes to produce silicon dust which is discharged from and reintroduced into the reaction chamber. The discharged silicon dust agglomerates with the silicon particles.



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